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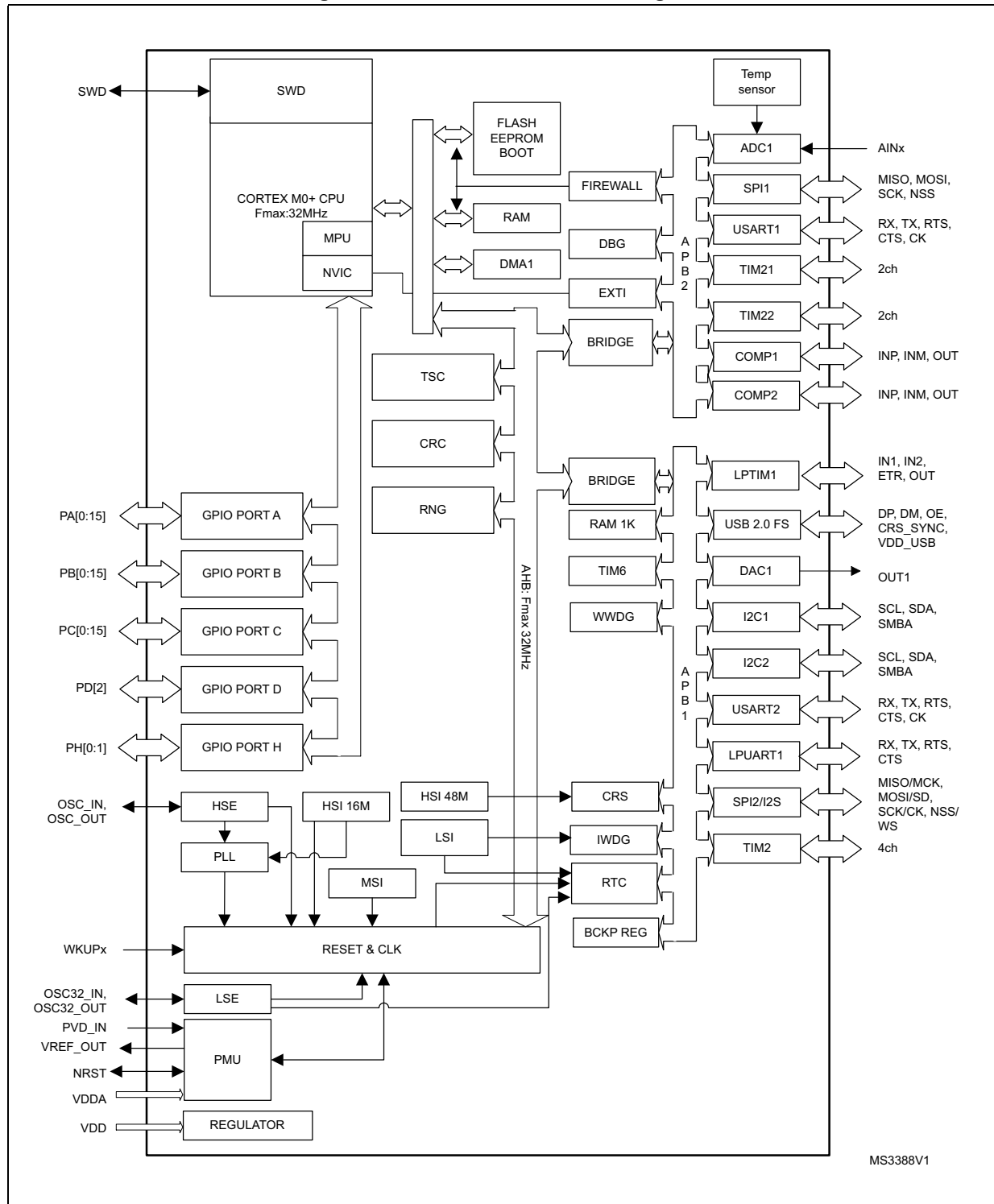
"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I ² C, IrDA, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, I ² S, POR, PWM, WDT
Number of I/O	51
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 16x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-TFBGA
Supplier Device Package	64-TFBGA (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l052r6h6

Figure 1. STM32L052x6/8 block diagram



- **Stop mode without RTC**

The Stop mode achieves the lowest power consumption while retaining the RAM and register contents. All clocks are stopped, the PLL, MSI RC, HSI and LSI RC, HSE and LSE crystal oscillators are disabled.

Some peripherals featuring wakeup capability can enable the HSI RC during Stop mode to detect their wakeup condition.

The voltage regulator is in the low-power mode. The device can be woken up from Stop mode by any of the EXTI line, in 3.5 μ s, the processor can serve the interrupt or resume the code. The EXTI line source can be any GPIO. It can be the PVD output, the comparator 1 event or comparator 2 event (if internal reference voltage is on). It can also be wakened by the USB/USART/I2C/LPUART/LPTIMER wakeup events.

- **Standby mode with RTC**

The Standby mode is used to achieve the lowest power consumption and real time clock. The internal voltage regulator is switched off so that the entire V_{CORE} domain is powered off. The PLL, MSI RC, HSE crystal and HSI RC oscillators are also switched off. The LSE or LSI is still running. After entering Standby mode, the RAM and register contents are lost except for registers in the Standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE Crystal 32 KHz oscillator, RCC_CSR register).

The device exits Standby mode in 60 μ s when an external reset (NRST pin), an IWDG reset, a rising edge on one of the three WKUP pins, RTC alarm (Alarm A or Alarm B), RTC tamper event, RTC timestamp event or RTC Wakeup event occurs.

- **Standby mode without RTC**

The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire V_{CORE} domain is powered off. The PLL, MSI RC, HSI and LSI RC, HSE and LSE crystal oscillators are also switched off. After entering Standby mode, the RAM and register contents are lost except for registers in the Standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE Crystal 32 KHz oscillator, RCC_CSR register).

The device exits Standby mode in 60 μ s when an external reset (NRST pin) or a rising edge on one of the three WKUP pin occurs.

Note: The RTC, the IWDG, and the corresponding clock sources are not stopped automatically by entering Stop or Standby mode.

**Table 5. Functionalities depending on the working mode
(from Run/active down to standby) ⁽¹⁾**

IPs	Run/Active	Sleep	Low-power run	Low-power sleep	Stop		Standby	
						Wakeup capability		Wakeup capability
CPU	Y	--	Y	--	--		--	
Flash memory	O	O	O	O	--		--	
RAM	Y	Y	Y	Y	Y		--	
Backup registers	Y	Y	Y	Y	Y		Y	
EEPROM	O	O	O	O	--		--	
Brown-out reset (BOR)	O	O	O	O	O	O	O	O
DMA	O	O	O	O	--		--	
Programmable Voltage Detector (PVD)	O	O	O	O	O	O	-	
Power-on/down reset (POR/PDR)	Y	Y	Y	Y	Y	Y	Y	Y
High Speed Internal (HSI)	O	O	--	--	⁽²⁾		--	
High Speed External (HSE)	O	O	O	O	--		--	
Low Speed Internal (LSI)	O	O	O	O	O		O	
Low Speed External (LSE)	O	O	O	O	O		O	
Multi-Speed Internal (MSI)	O	O	Y	Y	--		--	
Inter-Connect Controller	Y	Y	Y	Y	Y		--	
RTC	O	O	O	O	O	O	O	
RTC Tamper	O	O	O	O	O	O	O	O
Auto WakeUp (AWU)	O	O	O	O	O	O	O	O
USB	O	O	--	--	--	O	--	
USART	O	O	O	O	O ⁽³⁾	O	--	
LPUART	O	O	O	O	O ⁽³⁾	O	--	
SPI	O	O	O	O	--		--	
I2C	O	O	O	O	O ⁽⁴⁾	O	--	
ADC	O	O	--	--	--		--	
DAC	O	O	O	O	O		--	

**Table 5. Functionalities depending on the working mode
(from Run/active down to standby) (continued)⁽¹⁾**

IPs	Run/Active	Sleep	Low-power run	Low-power sleep	Stop		Standby	
						Wakeup capability		Wakeup capability
Temperature sensor	O	O	O	O	O		--	
Comparators	O	O	O	O	O	O	--	
16-bit timers	O	O	O	O	--		--	
LPTIMER	O	O	O	O	O	O		
IWDG	O	O	O	O	O	O	O	O
WWDG	O	O	O	O	--		--	
Touch sensing controller (TSC)	O	O	--	--	--		--	
SysTick Timer	O	O	O	O			--	
GPIOs	O	O	O	O	O	O		2 pins
Wakeup time to Run mode	0 μ s	0.36 μ s	3 μ s	32 μ s	3.5 μ s		50 μ s	
Consumption $V_{DD}=1.8$ to 3.6 V (Typ)	Down to 140 μ A/MHz (from Flash memory)	Down to 37 μ A/MHz (from Flash memory)	Down to 8 μ A	Down to 4.5 μ A	0.4 μ A (No RTC) $V_{DD}=1.8$ V		0.28 μ A (No RTC) $V_{DD}=1.8$ V	
					0.8 μ A (with RTC) $V_{DD}=1.8$ V		0.65 μ A (with RTC) $V_{DD}=1.8$ V	
					0.4 μ A (No RTC) $V_{DD}=3.0$ V		0.29 μ A (No RTC) $V_{DD}=3.0$ V	
					1 μ A (with RTC) $V_{DD}=3.0$ V		0.85 μ A (with RTC) $V_{DD}=3.0$ V	

- Legend:
 "Y" = Yes (enable).
 "O" = Optional can be enabled/disabled by software)
 "-" = Not available
- Some peripherals with wakeup from Stop capability can request HSI to be enabled. In this case, HSI is woken up by the peripheral, and only feeds the peripheral which requested it. HSI is automatically put off when the peripheral does not need it anymore.
- UART and LPUART reception is functional in Stop mode. It generates a wakeup interrupt on Start. To generate a wakeup on address match or received frame event, the LPUART can run on LSE clock while the UART has to wake up or keep running the HSI clock.
- I2C address detection is functional in Stop mode. It generates a wakeup interrupt in case of address match. It will wake up the HSI during reception.

3.2 Interconnect matrix

Several peripherals are directly interconnected. This allows autonomous communication between peripherals, thus saving CPU resources and power consumption. In addition, these hardware connections allow fast and predictable latency.

Depending on peripherals, these interconnections can operate in Run, Sleep, Low-power run, Low-power sleep and Stop modes.

Table 6. STM32L0xx peripherals interconnect matrix

Interconnect source	Interconnect destination	Interconnect action	Run	Sleep	Low-power run	Low-power sleep	Stop
COMPx	TIM2, TIM21, TIM22	Timer input channel, trigger from analog signals comparison	Y	Y	Y	Y	-
	LPTIM	Timer input channel, trigger from analog signals comparison	Y	Y	Y	Y	Y
TIMx	TIMx	Timer triggered by other timer	Y	Y	Y	Y	-
RTC	TIM21	Timer triggered by Auto wake-up	Y	Y	Y	Y	-
	LPTIM	Timer triggered by RTC event	Y	Y	Y	Y	Y
All clock source	TIMx	Clock source used as input channel for RC measurement and trimming	Y	Y	Y	Y	-
USB	CRS/HSI48	the clock recovery system trims the HSI48 based on USB SOF	Y	Y	-	-	-
GPIO	TIMx	Timer input channel and trigger	Y	Y	Y	Y	-
	LPTIM	Timer input channel and trigger	Y	Y	Y	Y	Y
	ADC, DAC	Conversion trigger	Y	Y	Y	Y	-

3.8 Memories

The STM32L052x6/8 devices have the following features:

- 8 Kbytes of embedded SRAM accessed (read/write) at CPU clock speed with 0 wait states. With the enhanced bus matrix, operating the RAM does not lead to any performance penalty during accesses to the system bus (AHB and APB buses).
- The non-volatile memory is divided into three arrays:
 - 32 or 64 Kbytes of embedded Flash program memory
 - 2 Kbytes of data EEPROM
 - Information block containing 32 user and factory options bytes plus 4 Kbytes of system memory

The user options bytes are used to write-protect or read-out protect the memory (with 4 Kbyte granularity) and/or readout-protect the whole memory with the following options:

- **Level 0:** no protection
- **Level 1:** memory readout protected.
The Flash memory cannot be read from or written to if either debug features are connected or boot in RAM is selected
- **Level 2:** chip readout protected, debug features (Cortex-M0+ serial wire) and boot in RAM selection disabled (debugline fuse)

The firewall protects parts of code/data from access by the rest of the code that is executed outside of the protected area. The granularity of the protected code segment or the non-volatile data segment is 256 bytes (Flash memory or EEPROM) against 64 bytes for the volatile data segment (RAM).

The whole non-volatile memory embeds the error correction code (ECC) feature.

3.9 Boot modes

At startup, BOOT0 pin and nBOOT1 option bit are used to select one of three boot options:

- Boot from Flash memory
- Boot from System memory
- Boot from embedded RAM

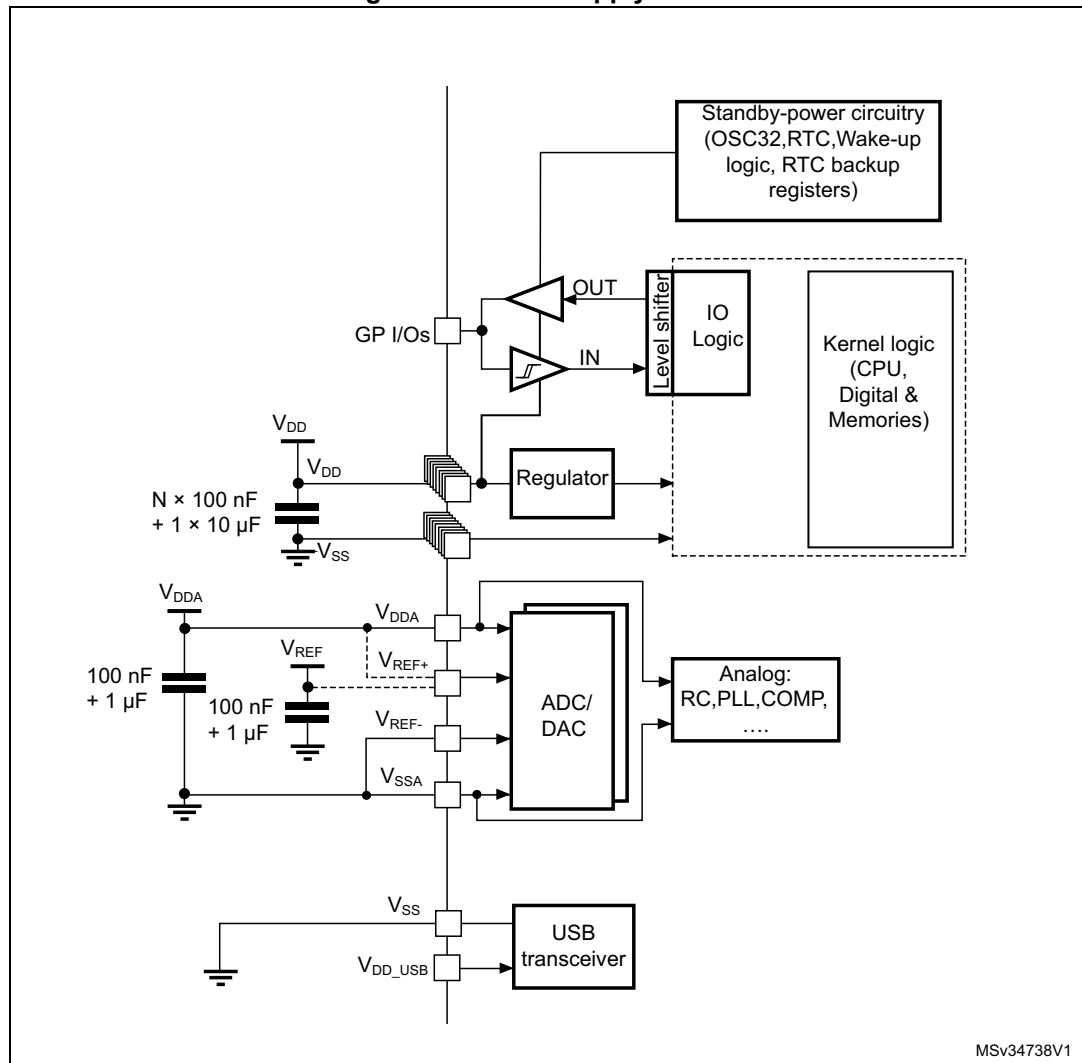
The boot loader is located in System memory. It is used to reprogram the Flash memory by using SPI1 (PA4, PA5, PA6, PA7) or SPI2 (PB12, PB13, PB14, PB15), USART1 (PA9, PA10) or USART2 (PA2, PA3). See STM32™ microcontroller system memory boot mode AN2606 for details.

Table 16. STM32L052x6/8 pin definitions (continued)

Pin Number						Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP32	UFQFN32	WLCSP36 ⁽¹⁾	LQFP48	LQFP64	TFBGA64						
-	-	-	5	5	C1	PH0-OSC_IN (PH0)	I/O	TC	-	USB_CRSS_SYNC	OSC_IN
-	-	-	6	6	D1	PH1-OSC_OUT (PH1)	I/O	TC	-	-	OSC_OUT
4	4	C6	7	7	E1	NRST	I/O	RST	-	-	-
-	-	-	-	8	E3	PC0	I/O	FT	-	LPTIM1_IN1, EVENTOUT, TSC_G7_IO1	ADC_IN10
-	-	-	-	9	E2	PC1	I/O	FT	-	LPTIM1_OUT, EVENTOUT, TSC_G7_IO2	ADC_IN11
-	-	-	-	10	F2	PC2	I/O	FT	-	LPTIM1_IN2, SPI2_MISO/I2S2_MC K, TSC_G7_IO3	ADC_IN12
-	-	-	-	11	-	PC3	I/O	FT	-	LPTIM1_ETR, SPI2_MOSI/I2S2_SD, TSC_G7_IO4	ADC_IN13
-	-	-	8	12	F1	VSSA	S	-	-	-	-
-	-	E6	-	-	G1	VREF+	S	-	-	-	-
5	5	D5	9	13	H1	VDDA	S	-	-	-	-
6	6	D4	10	14	G2	PA0	I/O	TC	-	TIM2_CH1, TSC_G1_IO1, USART2_CTS, TIM2_ETR, COMP1_OUT	COMP1_INM6 , ADC_IN0, RTC_TAMP2/ WKUP1
7	7	F6	11	15	H2	PA1	I/O	FT	-	EVENTOUT, TIM2_CH2, TSC_G1_IO2, USART2_RTS_DE, TIM21_ETR	COMP1_INP, ADC_IN1
8	8	E5	12	16	F3	PA2	I/O	FT	-	TIM21_CH1, TIM2_CH3, TSC_G1_IO3, USART2_TX, COMP2_OUT	COMP2_INM6 , ADC_IN2

6.1.6 Power supply scheme

Figure 12. Power supply scheme



6.1.7 Current consumption measurement

Figure 13. Current consumption measurement scheme

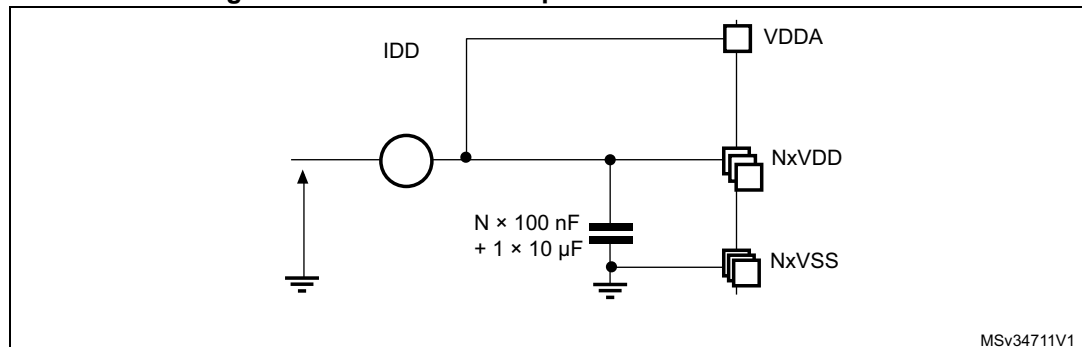


Table 36. Typical and maximum current consumptions in Stop mode

Symbol	Parameter	Conditions	Typ	Max ⁽¹⁾	Unit
I_{DD} (Stop)	Supply current in Stop mode	$T_A = -40$ to 25°C	0.41	1	μA
		$T_A = 55^\circ\text{C}$	0.63	2.1	
		$T_A = 85^\circ\text{C}$	1.7	4.5	
		$T_A = 105^\circ\text{C}$	4	9.6	
		$T_A = 125^\circ\text{C}$	11	24 ⁽²⁾	

1. Guaranteed by characterization results at 125°C , unless otherwise specified.

2. Guaranteed by test in production.

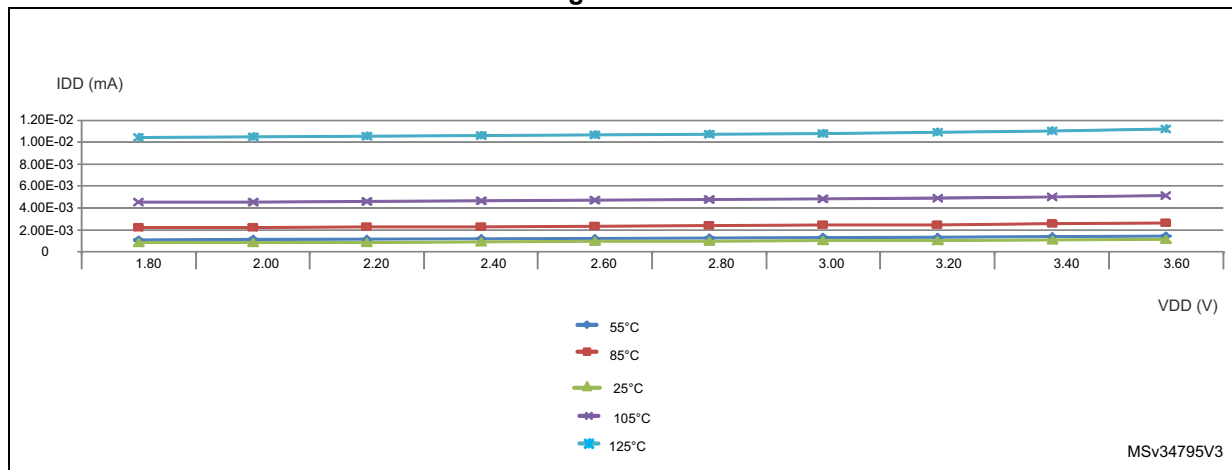
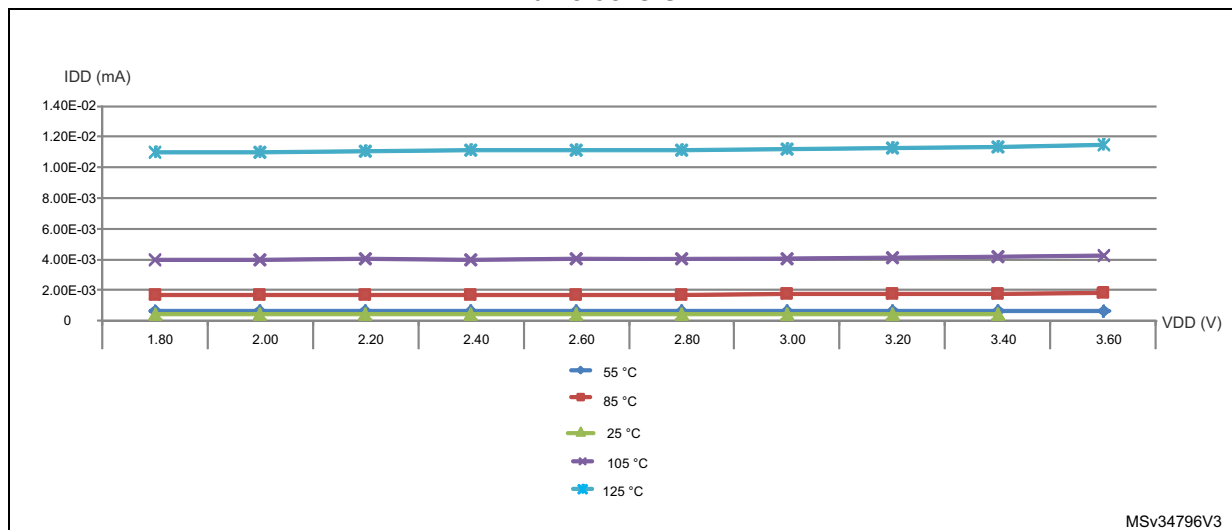
Figure 17. I_{DD} vs V_{DD} , at $T_A = 25/55/ 85/105/125^\circ\text{C}$, Stop mode with RTC enabled and running on LSE Low driveFigure 18. I_{DD} vs V_{DD} , at $T_A = 25/55/85/105/125^\circ\text{C}$, Stop mode with RTC disabled, all clocks OFF

Table 37. Typical and maximum current consumptions in Standby mode

Symbol	Parameter	Conditions	Typ	Max ⁽¹⁾	Unit
I _{DD} (Standby)	Supply current in Standby mode	Independent watchdog and LSI enabled	T _A = - 40 to 25°C	1.3	1.7
			T _A = 55 °C	-	2.9
			T _A = 85 °C	-	3.3
			T _A = 105 °C	-	4.1
			T _A = 125 °C	-	8.5
		Independent watchdog and LSI OFF	T _A = - 40 to 25°C	0.29	0.6
			T _A = 55 °C	0.32	0.9
			T _A = 85 °C	0.5	2.3
			T _A = 105 °C	0.94	3
			T _A = 125 °C	2.6	7

1. Guaranteed by characterization results at 125 °C, unless otherwise specified

Table 38. Average current consumption during Wakeup

Symbol	parameter	System frequency	Current consumption during wakeup	Unit
I _{DD} (Wakeup from Stop)	Supply current during Wakeup from Stop mode	HSI	1	mA
		HSI/4	0,7	
		MSI clock = 4,2 MHz	0,7	
		MSI clock = 1,05 MHz	0,4	
		MSI clock = 65 KHz	0,1	
I _{DD} (Reset)	Reset pin pulled down	-	0,21	
I _{DD} (Power-up)	BOR ON	-	0,23	
I _{DD} (Wakeup from StandBy)	With Fast wakeup set	MSI clock = 2,1 MHz	0,5	
	With Fast wakeup disabled	MSI clock = 2,1 MHz	0,12	

Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in [Table 45](#). In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

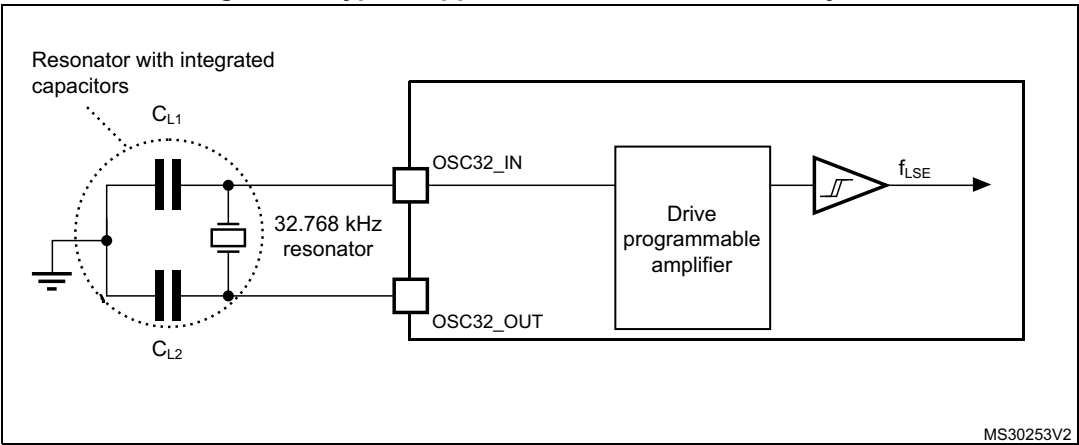
Table 45. LSE oscillator characteristics⁽¹⁾

Symbol	Parameter	Conditions ⁽²⁾	Min ⁽²⁾	Typ	Max	Unit
f_{LSE}	LSE oscillator frequency		-	32.768	-	kHz
G_m	Maximum critical crystal transconductance	LSEDRV[1:0]=00 lower driving capability	-	-	0.5	$\mu A/V$
		LSEDRV[1:0]= 01 medium low driving capability	-	-	0.75	
		LSEDRV[1:0] = 10 medium high driving capability	-	-	1.7	
		LSEDRV[1:0]=11 higher driving capability	-	-	2.7	
$t_{SU(LSE)}$ ⁽³⁾	Startup time	V_{DD} is stabilized	-	2	-	s

1. Guaranteed by design.
2. Refer to the note and caution paragraphs below the table, and to the application note AN2867 "Oscillator design guide for ST microcontrollers".
3. Guaranteed by characterization results. $t_{SU(LSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer. To increase speed, address a lower-drive quartz with a high- driver mode.

Note: For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

Figure 22. Typical application with a 32.768 kHz crystal



Note: An external resistor is not required between OSC32_IN and OSC32_OUT and it is forbidden to add one.

6.3.7 Internal clock source characteristics

The parameters given in [Table 46](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 25](#).

High-speed internal 16 MHz (HSI16) RC oscillator

Table 46. 16 MHz HSI16 oscillator characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI16}	Frequency	$V_{DD} = 3.0 \text{ V}$	-	16	-	MHz
$\text{TRIM}^{(1)(2)}$	HSI16 user-trimmed resolution	Trimming code is not a multiple of 16	-	± 0.4	0.7	%
		Trimming code is a multiple of 16	-	-	± 1.5	%
$\text{ACC}_{\text{HSI16}}^{(2)}$	Accuracy of the factory-calibrated HSI16 oscillator	$V_{DDA} = 3.0 \text{ V}$, $T_A = 25 \text{ }^\circ\text{C}$	-1 ⁽³⁾	-	1 ⁽³⁾	%
		$V_{DDA} = 3.0 \text{ V}$, $T_A = 0 \text{ to } 55 \text{ }^\circ\text{C}$	-1.5	-	1.5	%
		$V_{DDA} = 3.0 \text{ V}$, $T_A = -10 \text{ to } 70 \text{ }^\circ\text{C}$	-2	-	2	%
		$V_{DDA} = 3.0 \text{ V}$, $T_A = -10 \text{ to } 85 \text{ }^\circ\text{C}$	-2.5	-	2	%
		$V_{DDA} = 3.0 \text{ V}$, $T_A = -10 \text{ to } 105 \text{ }^\circ\text{C}$	-4	-	2	%
		$V_{DDA} = 1.65 \text{ V to } 3.6 \text{ V}$ $T_A = -40 \text{ to } 125 \text{ }^\circ\text{C}$	-5.45	-	3.25	%
$t_{\text{SU(HSI16)}}^{(2)}$	HSI16 oscillator startup time	-	-	3.7	6	μs
$I_{\text{DD(HSI16)}}^{(2)}$	HSI16 oscillator power consumption	-	-	100	140	μA

1. The trimming step differs depending on the trimming code. It is usually negative on the codes which are multiples of 16 (0x00, 0x10, 0x20, 0x30...0xE0).
2. Guaranteed by characterization results.
3. Guaranteed by test in production.

Figure 23. HSI16 minimum and maximum value versus temperature

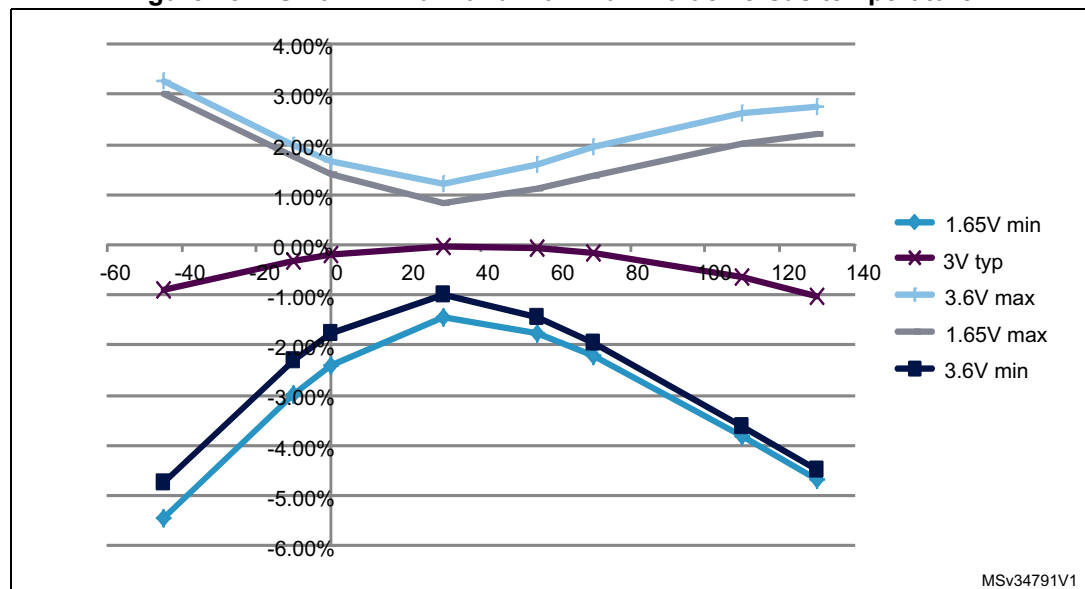
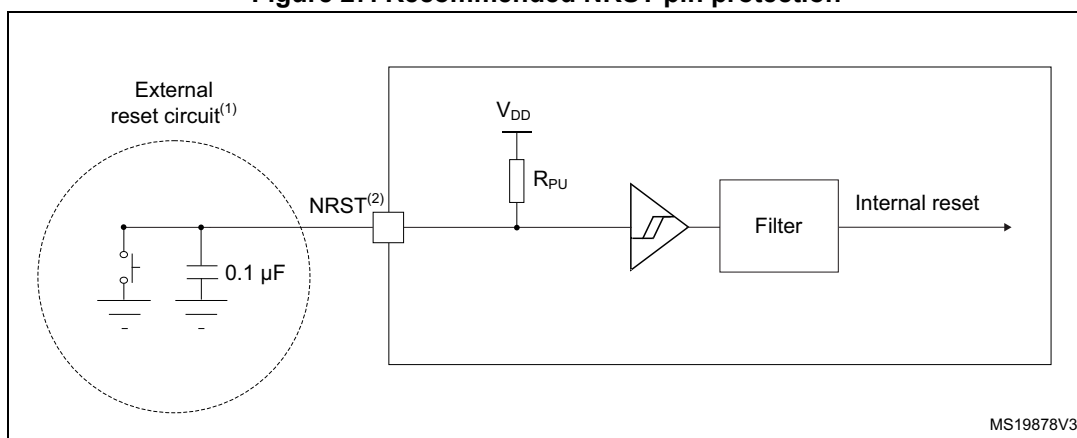


Figure 27. Recommended NRST pin protection



1. The reset network protects the device against parasitic resets.
2. The external capacitor must be placed as close as possible to the device.
3. The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in [Table 62](#). Otherwise the reset will not be taken into account by the device.

6.3.15 12-bit ADC characteristics

Unless otherwise specified, the parameters given in [Table 63](#) are derived from tests performed under ambient temperature, f_{PCLK} frequency and V_{DDA} supply voltage conditions summarized in [Table 25: General operating conditions](#).

Note: *It is recommended to perform a calibration after each power-up.*

Table 63. ADC characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DDA}	Analog supply voltage for ADC ON	Fast channel	1.65	-	3.6	V
		Standard channel	1.75 ⁽¹⁾	-	3.6	
$I_{DDA(ADC)}$	Current consumption of the ADC on V_{DDA} and V_{REF+}	1.14 Msps	-	200	-	μA
		10 ksps	-	40	-	
	Current consumption of the ADC on V_{DD} ⁽²⁾	1.14 Msps	-	70	-	
		10 ksps	-	1	-	
f_{ADC}	ADC clock frequency	Voltage scaling Range 1	0.14	-	16	MHz
		Voltage scaling Range 2	0.14	-	8	
		Voltage scaling Range 3	0.14	-	4	
$f_S^{(3)}$	Sampling rate	12-bit resolution	0.01	-	1.14	MHz
$f_{TRIG}^{(3)}$	External trigger frequency	$f_{ADC} = 16$ MHz, 12-bit resolution	-	-	941	kHz
		-	-	-	17	1/ f_{ADC}
V_{AIN}	Conversion voltage range	-	0	-		V
$R_{AIN}^{(3)}$	External input impedance	See Equation 1 and Table 64 for details	-	-	50	k Ω

Table 63. ADC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{ADC}^{(3)(4)}$	Sampling switch resistance	-	-	-	1	k Ω
$C_{ADC}^{(3)}$	Internal sample and hold capacitor	-	-	-	8	pF
$t_{CAL}^{(3)(5)}$	Calibration time	$f_{ADC} = 16$ MHz	5.2			μ s
		-	83			$1/f_{ADC}$
$W_{LATENCY}^{(6)}$	ADC_DR register write latency	ADC clock = HSI16	1.5 ADC cycles + 2 f_{PCLK} cycles	-	1.5 ADC cycles + 3 f_{PCLK} cycles	-
		ADC clock = PCLK/2	-	4.5	-	f_{PCLK} cycle
		ADC clock = PCLK/4	-	8.5	-	f_{PCLK} cycle
$t_{latr}^{(3)}$	Trigger conversion latency	$f_{ADC} = f_{PCLK}/2 = 16$ MHz	0.266			μ s
		$f_{ADC} = f_{PCLK}/2$	8.5			$1/f_{PCLK}$
		$f_{ADC} = f_{PCLK}/4 = 8$ MHz	0.516			μ s
		$f_{ADC} = f_{PCLK}/4$	16.5			$1/f_{PCLK}$
		$f_{ADC} = f_{HSI16} = 16$ MHz	0.252	-	0.260	μ s
Jitter _{ADC}	ADC jitter on trigger conversion	$f_{ADC} = f_{HSI16}$	-	1	-	$1/f_{HSI16}$
$t_S^{(3)}$	Sampling time	$f_{ADC} = 16$ MHz	0.093	-	10.03	μ s
		-	1.5	-	160.5	$1/f_{ADC}$
$t_{UP_LDO}^{(3)(5)}$	Internal LDO power-up time	-	-	-	10	μ s
$t_{STAB}^{(3)(5)}$	ADC stabilization time	-	14			$1/f_{ADC}$
$t_{ConV}^{(3)}$	Total conversion time (including sampling time)	$f_{ADC} = 16$ MHz, 12-bit resolution	0.875	-	10.81	μ s
		12-bit resolution	14 to 173 (t_S for sampling + 12.5 for successive approximation)			$1/f_{ADC}$

1. V_{DDA} minimum value can be decreased in specific temperature conditions. Refer to [Table 64: RAIN max for \$f_{ADC} = 16\$ MHz](#).
2. A current consumption proportional to the APB clock frequency has to be added (see [Table 39: Peripheral current consumption in Run or Sleep mode](#)).
3. Guaranteed by design.
4. Standard channels have an extra protection resistance which depends on supply voltage. Refer to [Table 64: RAIN max for \$f_{ADC} = 16\$ MHz](#).
5. This parameter only includes the ADC timing. It does not take into account register access latency.
6. This parameter specifies the latency to transfer the conversion result into the ADC_DR register. EOC bit is set to indicate the conversion is complete and has the same latency.

6.3.17 Temperature sensor characteristics

Table 67. Temperature sensor calibration values

Calibration value name	Description	Memory address
TS_CAL1	TS ADC raw data acquired at temperature of 30 °C, $V_{DDA} = 3\text{ V}$	0x1FF8 007A - 0x1FF8 007B
TS_CAL2	TS ADC raw data acquired at temperature of 130 °C, $V_{DDA} = 3\text{ V}$	0x1FF8 007E - 0x1FF8 007F

Table 68. Temperature sensor characteristics

Symbol	Parameter	Min	Typ	Max	Unit
$T_L^{(1)}$	V_{SENSE} linearity with temperature	-	± 1	± 2	°C
Avg_Slope ⁽¹⁾	Average slope	1.48	1.61	1.75	mV/°C
V_{130}	Voltage at 130°C $\pm 5^\circ\text{C}^{(2)}$	640	670	700	mV
$I_{DDA(TEMP)}^{(3)}$	Current consumption	-	3.4	6	μA
$t_{START}^{(3)}$	Startup time	-	-	10	μs
$T_{S_temp}^{(4)(3)}$	ADC sampling time when reading the temperature	10	-	-	

1. Guaranteed by characterization results.
2. Measured at $V_{DD} = 3\text{ V} \pm 10\text{ mV}$. V_{130} ADC conversion result is stored in the TS_CAL2 byte.
3. Guaranteed by design.
4. Shortest sampling time can be determined in the application by multiple iterations.

6.3.18 Comparators

Table 69. Comparator 1 characteristics

Symbol	Parameter	Conditions	Min ⁽¹⁾	Typ	Max ⁽¹⁾	Unit
V_{DDA}	Analog supply voltage	-	1.65		3.6	V
R_{400K}	R_{400K} value	-	-	400	-	kΩ
R_{10K}	R_{10K} value	-	-	10	-	
V_{IN}	Comparator 1 input voltage range	-	0.6	-	V_{DDA}	V
t_{START}	Comparator startup time	-	-	7	10	μs
t_d	Propagation delay ⁽²⁾	-	-	3	10	
V_{offset}	Comparator offset	-	-	± 3	± 10	mV
$d_{V_{offset}}/dt$	Comparator offset variation in worst voltage stress conditions	$V_{DDA} = 3.6\text{ V}$, $V_{IN+} = 0\text{ V}$, $V_{IN-} = V_{REFINT}$, $T_A = 25^\circ\text{C}$	0	1.5	10	mV/1000 h
I_{COMP1}	Current consumption ⁽³⁾	-	-	160	260	nA

1. Guaranteed by characterization.
2. The delay is characterized for 100 mV input step with 10 mV overdrive on the inverting input, the non-inverting input set to the reference.
3. Comparator consumption only. Internal reference voltage not included.

The analog spike filter is compliant with I²C timings requirements only for the following voltage ranges:

- Fast mode Plus: $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$ and voltage scaling Range 1
- Fast mode:
 - $2\text{ V} \leq V_{DD} \leq 3.6\text{ V}$ and voltage scaling Range 1 or Range 2.
 - $V_{DD} < 2\text{ V}$, voltage scaling Range 1 or Range 2, $C_{load} < 200\text{ pF}$.

In other ranges, the analog filter should be disabled. The digital filter can be used instead.

Note: In Standard mode, no spike filter is required.

Table 72. I2C analog filter characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit
t_{AF}	Maximum pulse width of spikes that are suppressed by the analog filter	Range 1	50 ⁽²⁾	260 ⁽³⁾	ns
		Range 2		-	
		Range 3		-	

1. Guaranteed by characterization results.
2. Spikes with widths below $t_{AF(min)}$ are filtered.
3. Spikes with widths above $t_{AF(max)}$ are not filtered

USART/LPUART characteristics

The parameters given in the following table are guaranteed by design.

Table 73. USART/LPUART characteristics

Symbol	Parameter	Conditions	Typ	Max	Unit
$t_{WUUSART}$	Wakeup time needed to calculate the maximum USART/LPUART baudrate allowing to wake up from Stop mode when the USART/LPUART is clocked by HSI	Stop mode with main regulator in Run mode, Range 2 or 3	-	8.7	μs
		Stop mode with main regulator in Run mode, Range 1	-	8.1	
		Stop mode with main regulator in low-power mode, Range 2 or 3	-	12	
		Stop mode with main regulator in low-power mode, Range 1	-	11.4	

Table 76. SPI characteristics in voltage Range 3 ⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{SCK} $1/t_{c(SCK)}$	SPI clock frequency	Master mode	-	-	2	MHz
		Slave mode			$2^{(2)}$	
$Duty_{(SCK)}$	Duty cycle of SPI clock frequency	Slave mode	30	50	70	%
$t_{su(NSS)}$	NSS setup time	Slave mode, SPI presc = 2	$4 \cdot T_{pclk}$	-	-	ns
$t_{h(NSS)}$	NSS hold time	Slave mode, SPI presc = 2	$2 \cdot T_{pclk}$	-	-	
$t_{w(SCKH)}$ $t_{w(SCKL)}$	SCK high and low time	Master mode	$T_{pclk}-2$	T_{pclk}	$T_{pclk}+2$	
$t_{su(MI)}$	Data input setup time	Master mode	1.5	-	-	
$t_{su(SI)}$		Slave mode	6	-	-	
$t_{h(MI)}$	Data input hold time	Master mode	13.5	-	-	
$t_{h(SI)}$		Slave mode	16	-	-	
$t_{a(SO)}$	Data output access time	Slave mode	30	-	70	
$t_{dis(SO)}$	Data output disable time	Slave mode	40	-	80	
$t_{v(SO)}$	Data output valid time	Slave mode	-	30	70	
$t_{v(MO)}$		Master mode	-	7	9	
$t_{h(SO)}$	Data output hold time	Slave mode	25	-	-	
$t_{h(MO)}$		Master mode	8	-	-	

1. Guaranteed by characterization results.

2. The maximum SPI clock frequency in slave transmitter mode is determined by the sum of $t_{v(SO)}$ and $t_{su(MI)}$ which has to fit into SCK low or high phase preceding the SCK sampling edge. This value can be achieved when the SPI communicates with a master having $t_{su(MI)} = 0$ while $Duty_{(SCK)} = 50\%$.

USB characteristics

The USB interface is USB-IF certified (full speed).

Table 78. USB startup time

Symbol	Parameter	Max	Unit
$t_{\text{STARTUP}}^{(1)}$	USB transceiver startup time	1	μs

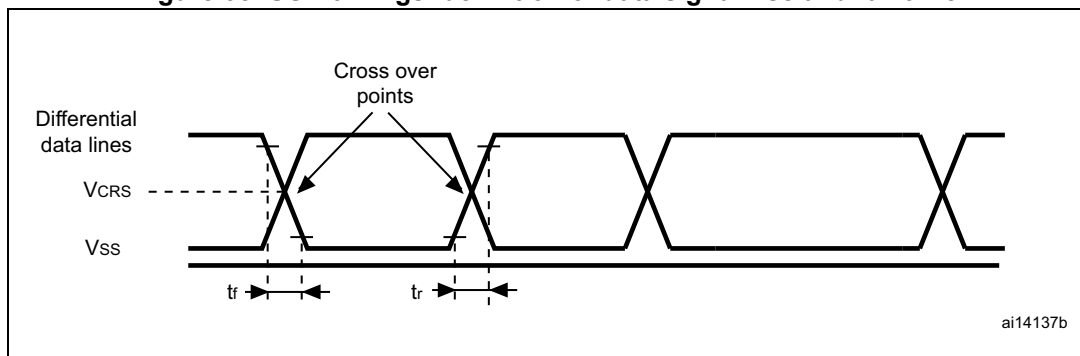
1. Guaranteed by design.

Table 79. USB DC electrical characteristics

Symbol	Parameter	Conditions	Min. ⁽¹⁾	Max. ⁽¹⁾	Unit
Input levels					
V _{DD}	USB operating voltage	-	3.0	3.6	V
V _{DI} ⁽²⁾	Differential input sensitivity	I(USB_DP, USB_DM)	0.2	-	V
V _{CM} ⁽²⁾	Differential common mode range	Includes V _{DI} range	0.8	2.5	
V _{SE} ⁽²⁾	Single ended receiver threshold	-	1.3	2.0	
Output levels					
V _{OL} ⁽³⁾	Static output level low	R _L of 1.5 kΩ to 3.6 V ⁽⁴⁾	-	0.3	V
V _{OH} ⁽³⁾	Static output level high	R _L of 15 kΩ to V _{SS} ⁽⁴⁾	2.8	3.6	

1. All the voltages are measured from the local ground potential.
2. Guaranteed by characterization results.
3. Guaranteed by test in production.
4. R_{L} is the load connected on the USB drivers.

Figure 38. USB timings: definition of data signal rise and fall time



7.8 Thermal characteristics

The maximum chip-junction temperature, $T_J \text{ max}$, in degrees Celsius, may be calculated using the following equation:

$$T_J \text{ max} = T_A \text{ max} + (P_D \text{ max} \times \Theta_{JA})$$

Where:

- $T_A \text{ max}$ is the maximum ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,
- $P_D \text{ max}$ is the sum of $P_{INT} \text{ max}$ and $P_{I/O} \text{ max}$ ($P_D \text{ max} = P_{INT} \text{ max} + P_{I/O} \text{ max}$),
- $P_{INT} \text{ max}$ is the product of I_{DD} and V_{DD} , expressed in Watts. This is the maximum chip internal power.

$P_{I/O} \text{ max}$ represents the maximum power dissipation on output pins where:

$$P_{I/O} \text{ max} = \Sigma (V_{OL} \times I_{OL}) + \Sigma (V_{DD} - V_{OH}) \times I_{OH},$$

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

Table 91. Thermal characteristics

Symbol	Parameter	Value	Unit
Θ_{JA}	Thermal resistance junction-ambient TFBGA64 - 5 x 5 mm / 0.5 mm pitch	61	°C/W
	Thermal resistance junction-ambient LQFP64 - 10 x 10 mm / 0.5 mm pitch	45	
	Thermal resistance junction-ambient Standard WLCSP36 - 0.4 mm pitch	63	
	Thermal resistance junction-ambient Thin WLCSP36 - 0.4 mm pitch	59	
	Thermal resistance junction-ambient LQFP48 - 7 x 7 mm / 0.5 mm pitch	55	
	Thermal resistance junction-ambient LQFP32 - 7 x 7 mm / 0.8 mm pitch	57	
	Thermal resistance junction-ambient UFQFPN32 - 5 x 5 mm / 0.5 mm pitch	38	

Table 93. Document revision history (continued)

Date	Revision	Changes
05-Sep-2014	4	<p>Extended operating temperature range to 125 °C.</p> <p>Updated minimum ADC operating voltage to 1.65 V.</p> <p>Changed number of I2S interface from 1 to 0 in Table 2: Ultra-low-power STM32L052x6/x8 device features and peripheral counts.</p> <p>Replaced USART3 by LPUART1 in Table 16: STM32L052x6/8 pin definitions and LPUART by LPUART1 in Table 17: Alternate function port A, Table 18: Alternate function port B, Table 19: Alternate function port C, Table 20: Alternate function port D and Table 21: Alternate function port H. Updated PA6 in Table 17: Alternate function port A.</p> <p>Updated temperature range in Section 1: Description, Table 2: Ultra-low-power STM32L052x6/x8 device features and peripheral counts.</p> <p>Updated P_D, T_A and T_J to add range 3 in Table 25: General operating conditions. Added range 3 in Table 53: Flash memory and data EEPROM endurance and retention, Table 92: STM32L052x6/8 ordering information scheme. Update note 1 in Table 29: Current consumption in Run mode, code with data processing running from Flash, Table 31: Current consumption in Run mode, code with data processing running from RAM, Table 33: Current consumption in Sleep mode, Table 34: Current consumption in Low-power run mode, Table 34: Current consumption in Low-power run mode, Table 36: Typical and maximum current consumptions in Stop mode, Table 37: Typical and maximum current consumptions in Standby mode and Table 41: Low-power mode wakeup timings. Updated Figure 59: Thermal resistance and removed note 1. Updated Figure 16: IDD vs VDD, at TA= 25/55/ 85/105/125 °C, Low-power run mode, code running from RAM, Range 3, MSI (Range 0) at 64 KHz, 0 WS, Figure 17: IDD vs VDD, at TA= 25/55/ 85/105/125 °C, Stop mode with RTC enabled and running on LSE Low drive, Figure 18: IDD vs VDD, at TA= 25/55/85/105/125 °C, Stop mode with RTC disabled, all clocks OFF.</p> <p>Updated Table 37: Typical and maximum current consumptions in Standby mode.</p> <p>Updated SYSCFG in Table 39: Peripheral current consumption in Run or Sleep mode.</p> <p>Updated Table 40: Peripheral current consumption in Stop and Standby mode and Table 43: Low-speed external user clock characteristics.</p> <p>Updated ACC_{HSI16} temperature conditions in Table 46: 16 MHz HSI16 oscillator characteristics. Changed ambient temperature range in note 1 below Table 47: HSI48 oscillator characteristics.</p> <p>Updated V_{F(NRST)} and V_{NF(NRST)} in Table 62: NRST pin characteristics.</p> <p>Updated Table 63: ADC characteristics and Table 65: ADC accuracy.</p> <p>Added range 3 in Table 92: STM32L052x6/8 ordering information scheme.</p>